

Serial No.: 10/003,287
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IN THE ABSTRACT:

Please amend the abstract as follows:

--ABSTRACT

A method of fabricating an exposure mask for semiconductor manufacture to improve the accuracy of critical dimensions of the mask pattern. The method includes including the steps of forming a chrome layer, a first photo resist, an Ag layer as a conductive layer and a second photo resist on a transparent quartz substrate, in sequence; forming and using a second photo resist pattern ~~by exposing and developing the second photo resist; forming to form~~ a conductive layer pattern by etching the conductive layer ~~using the second photo resist pattern as an etch barrier;~~ removing the second photo resist pattern; forming an oxide layer ~~as a layer for shielding light at the surface of the conductive layer pattern and by oxidizing the conductive layer pattern;~~ exposing the first photo resist using the conductive layer pattern with having the oxide layer thereon ~~at the surface thereof;~~ forming a first photo resist pattern exposing the chrome layer ~~and by developing the exposed first photo resist;~~ forming a mask pattern including the chrome layer by selectively etching the exposed chrome layer parts; and removing the conductive layer pattern including the oxide layer and the first photo resist pattern.--